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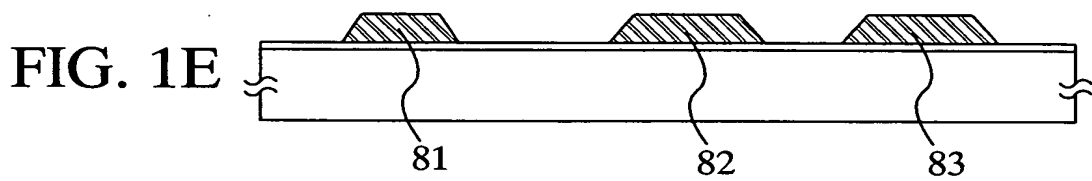
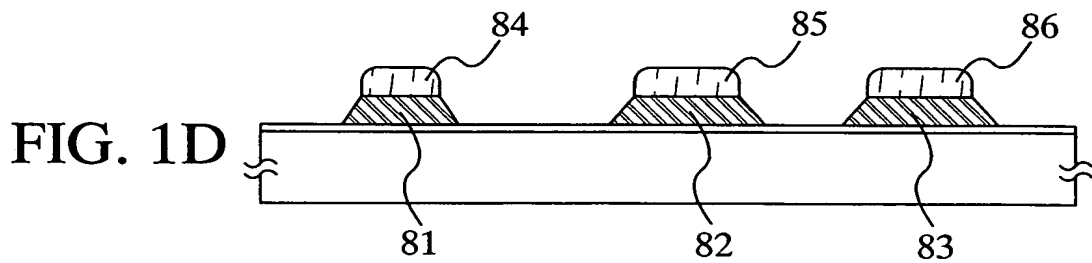
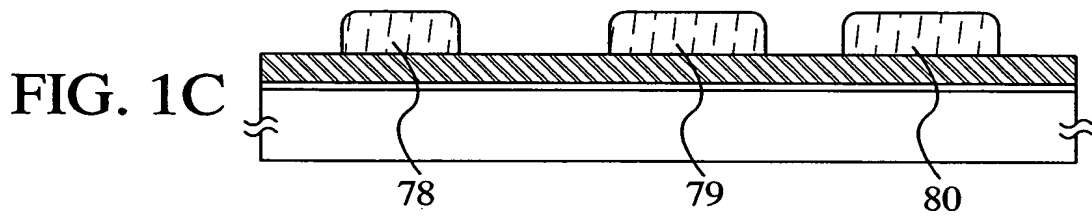
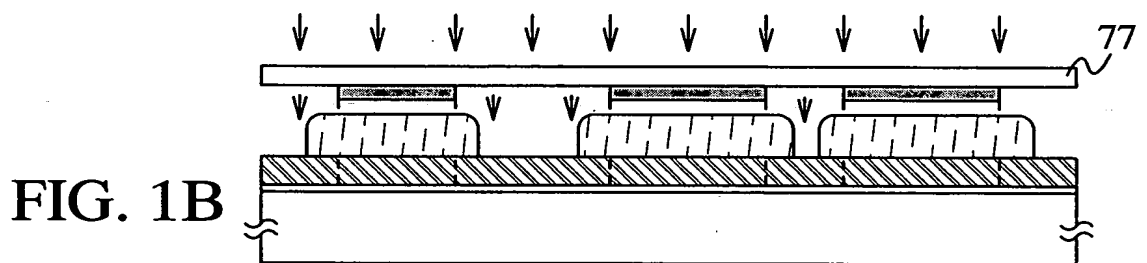
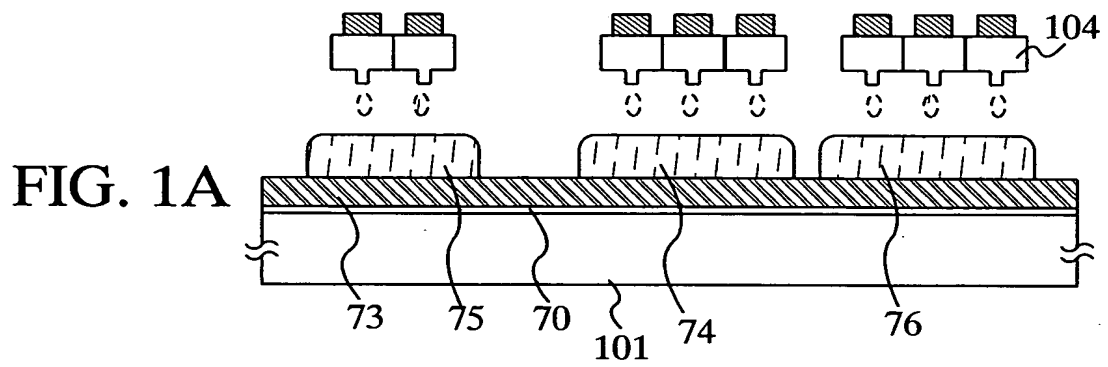
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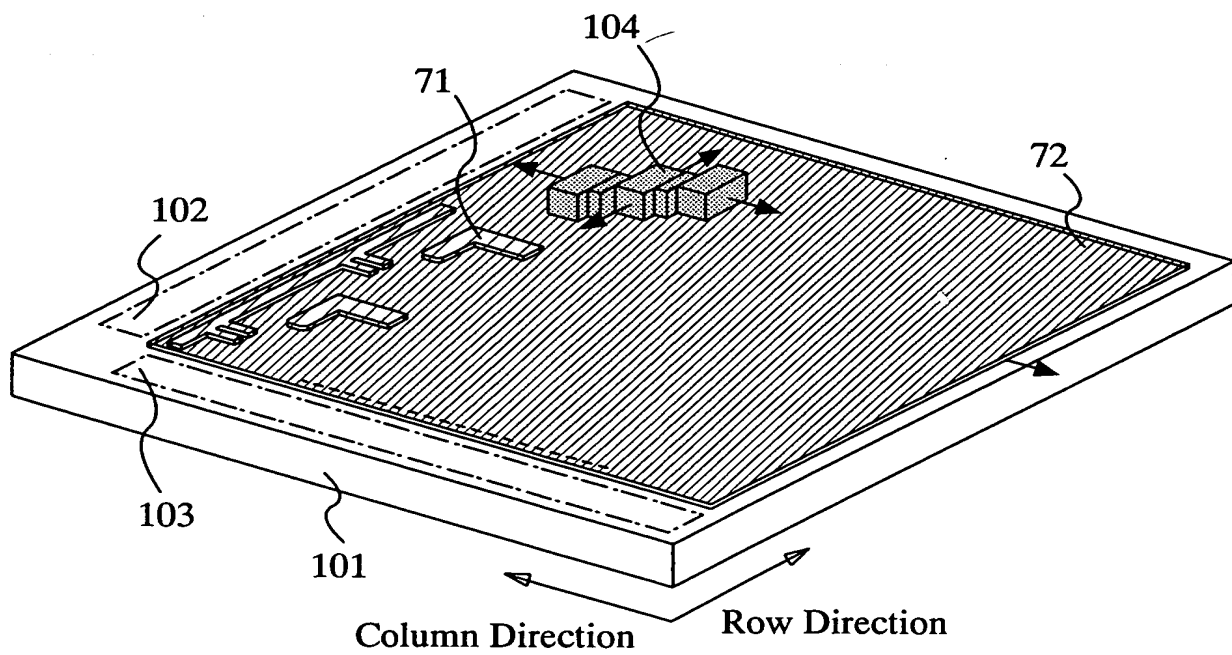


FIG. 2

FIG. 3A

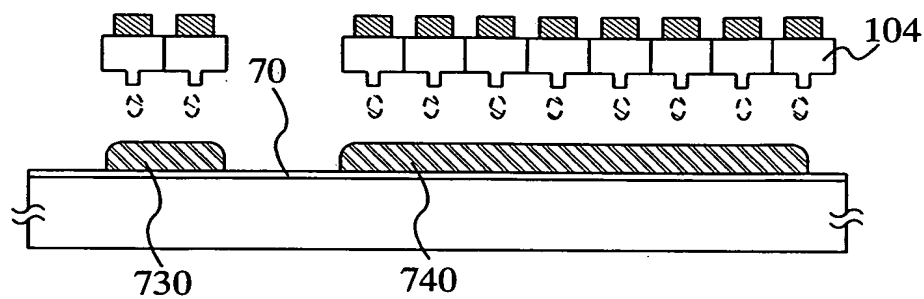


FIG. 3B

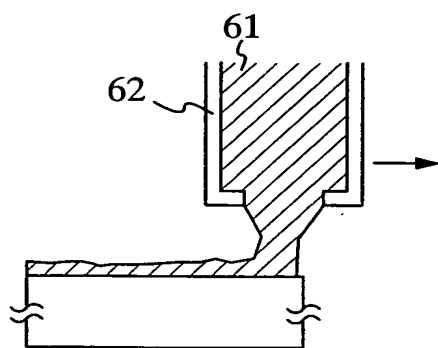
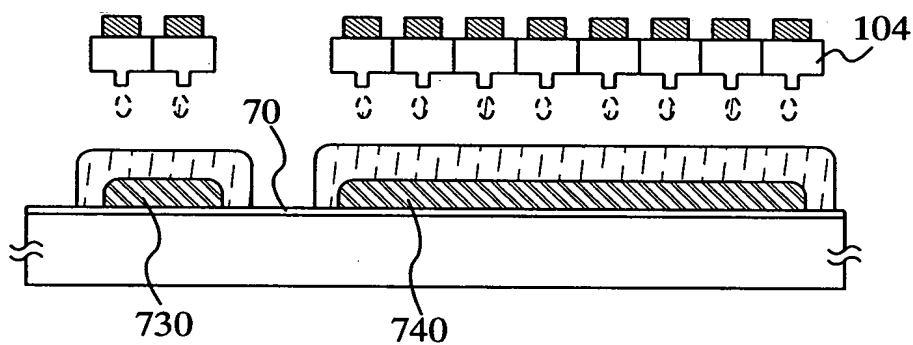


FIG. 3C

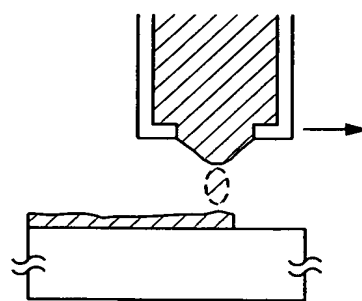


FIG. 3D

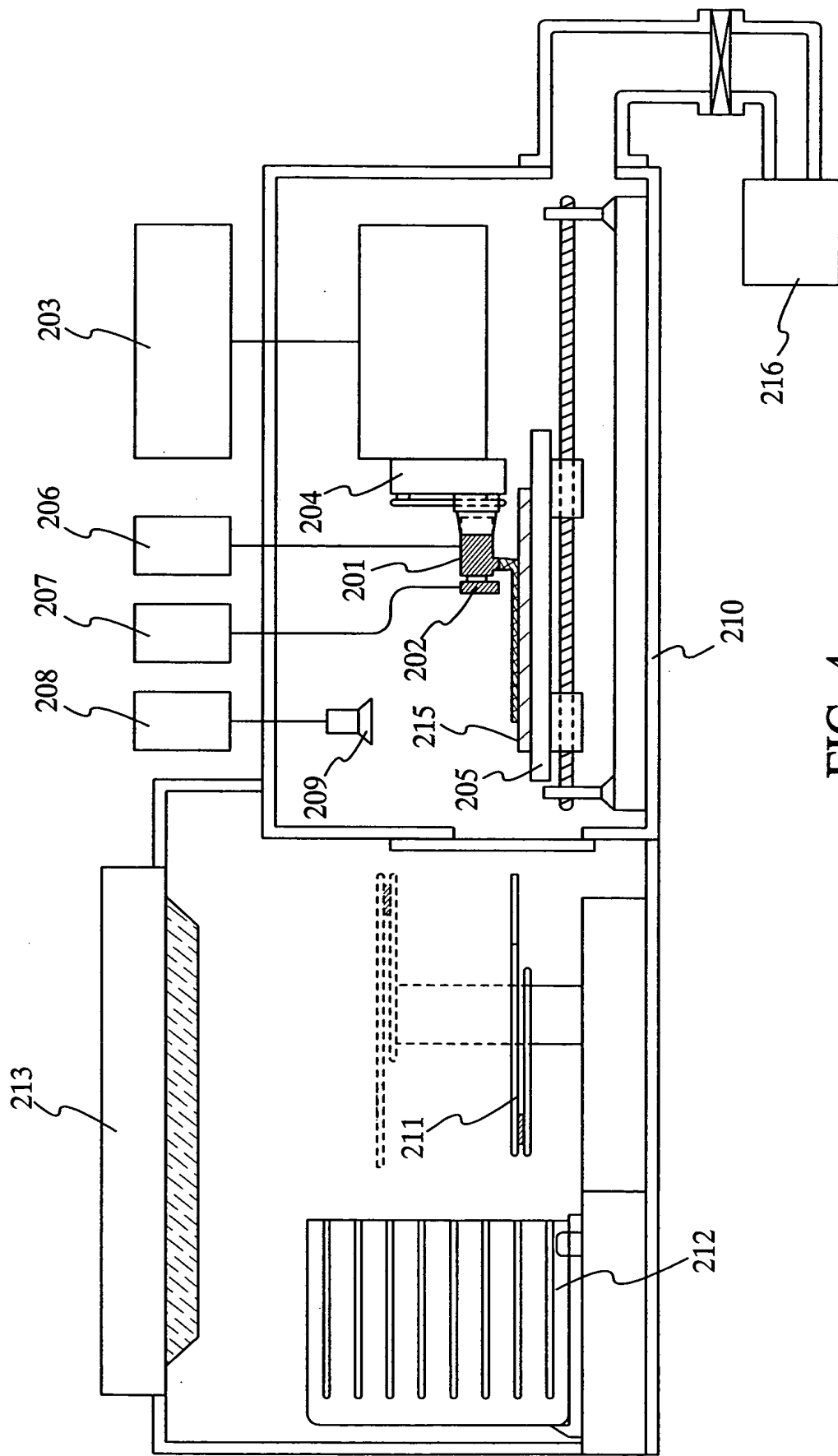


FIG. 4

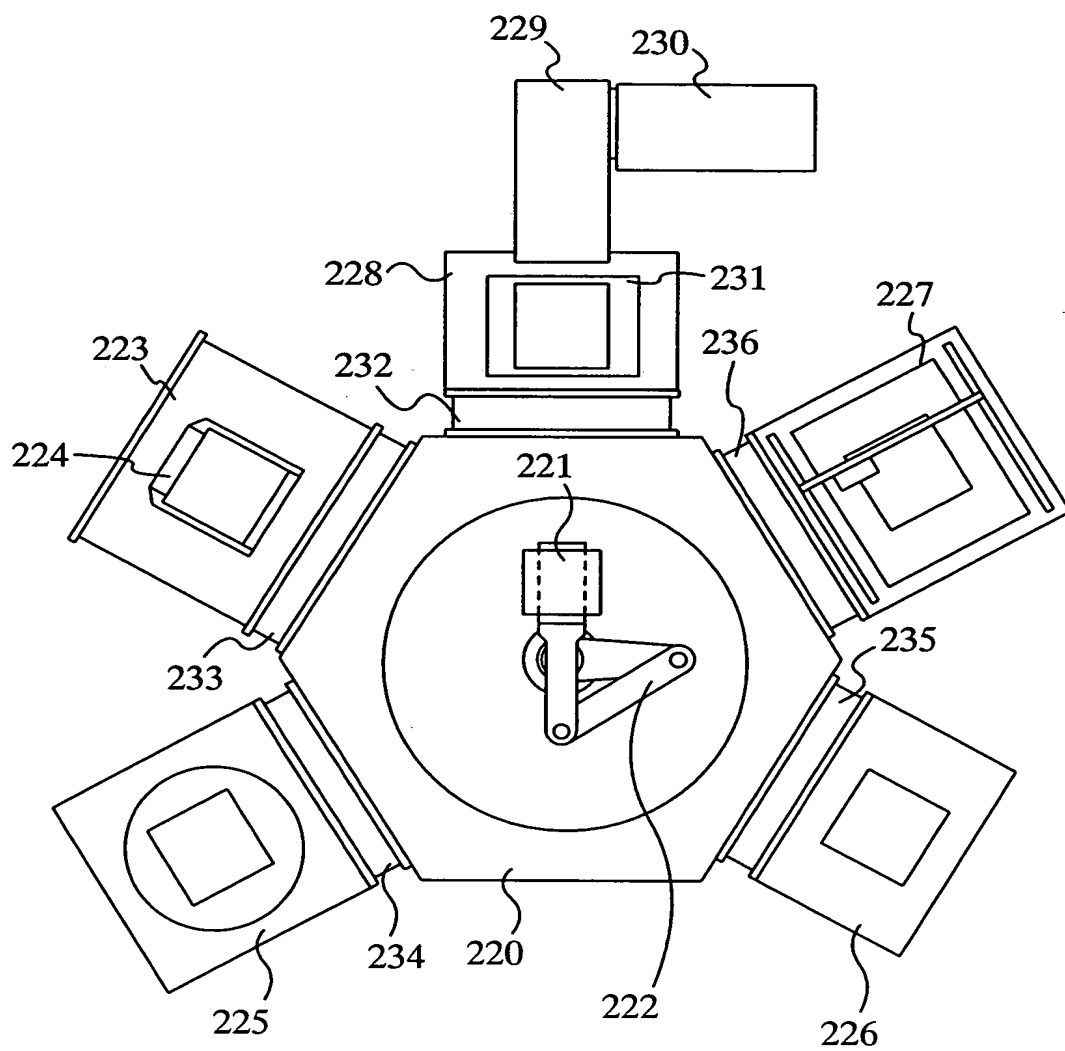


FIG. 5

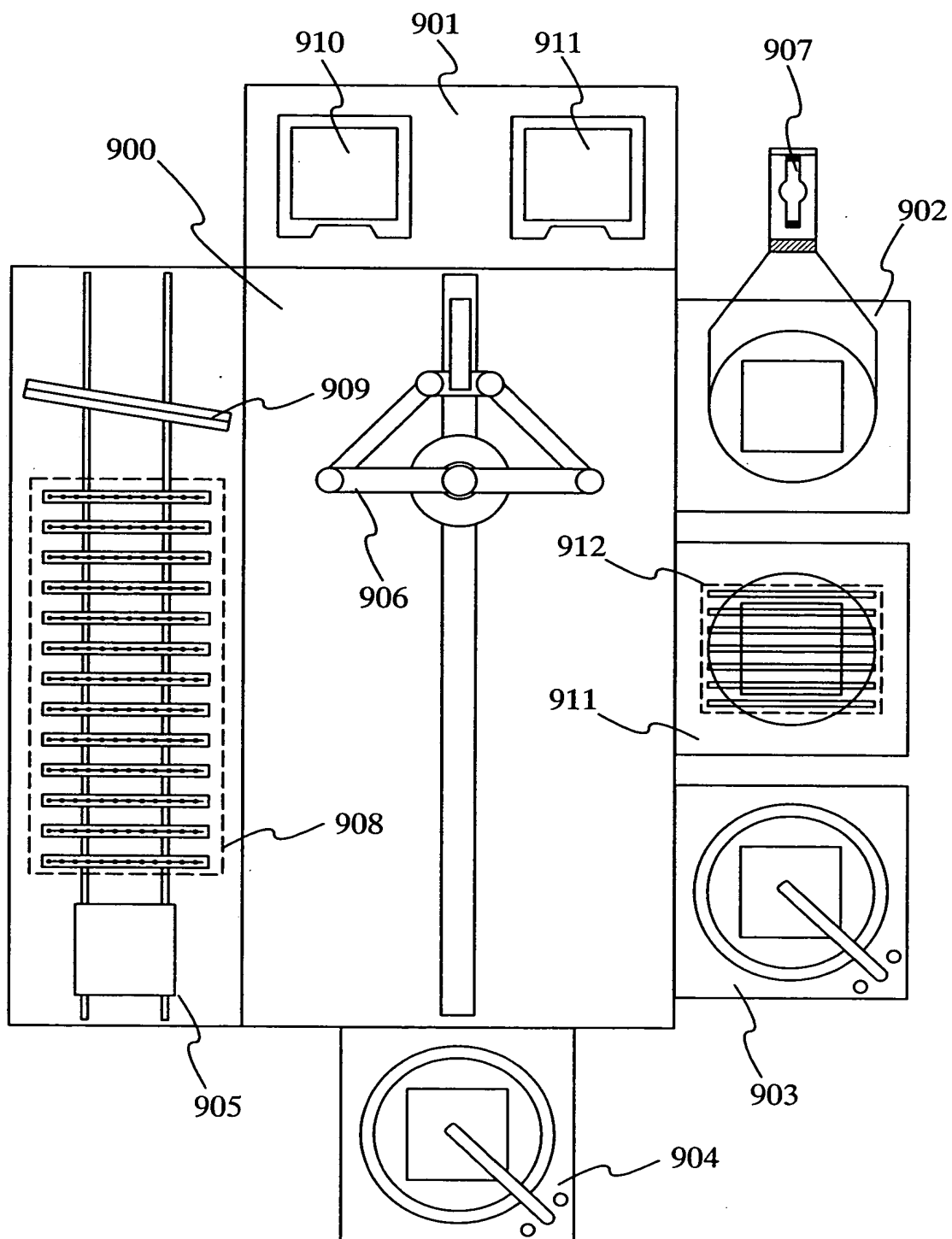


FIG. 6

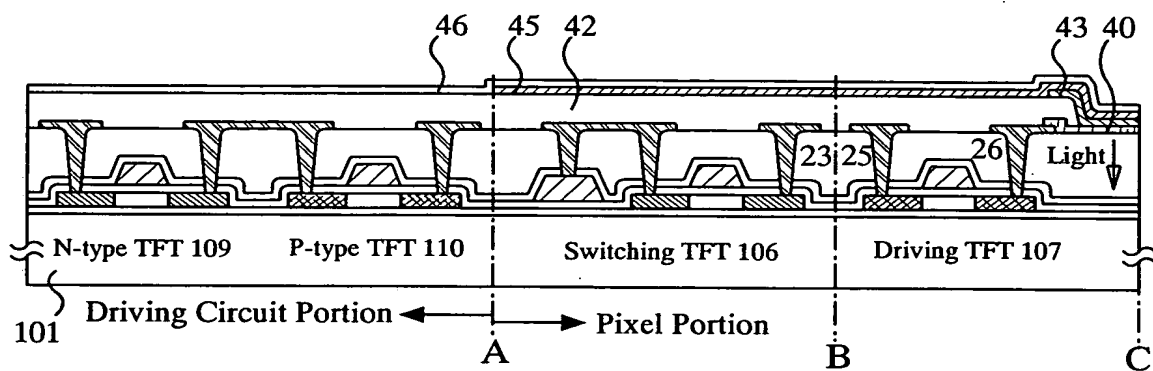


FIG. 7A

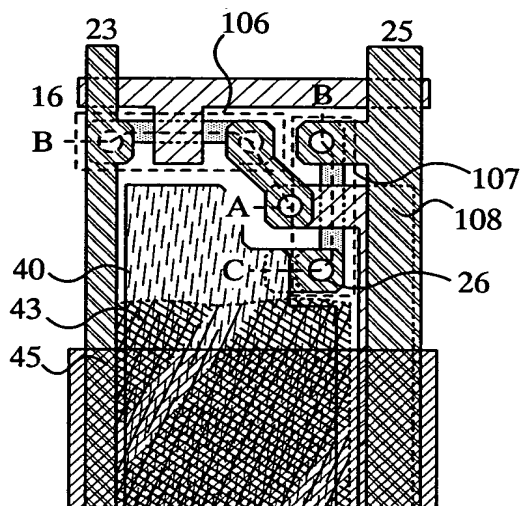


FIG. 7B

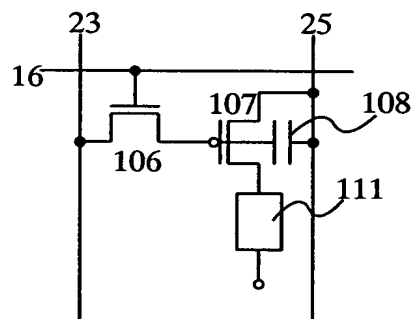


FIG. 7C

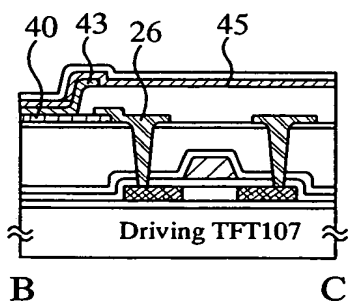


FIG. 7D

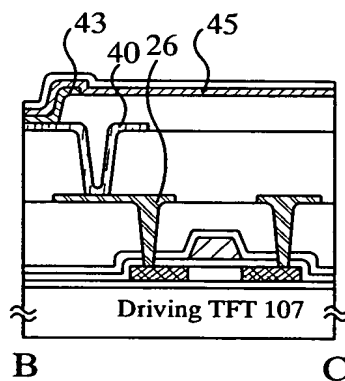


FIG. 7E

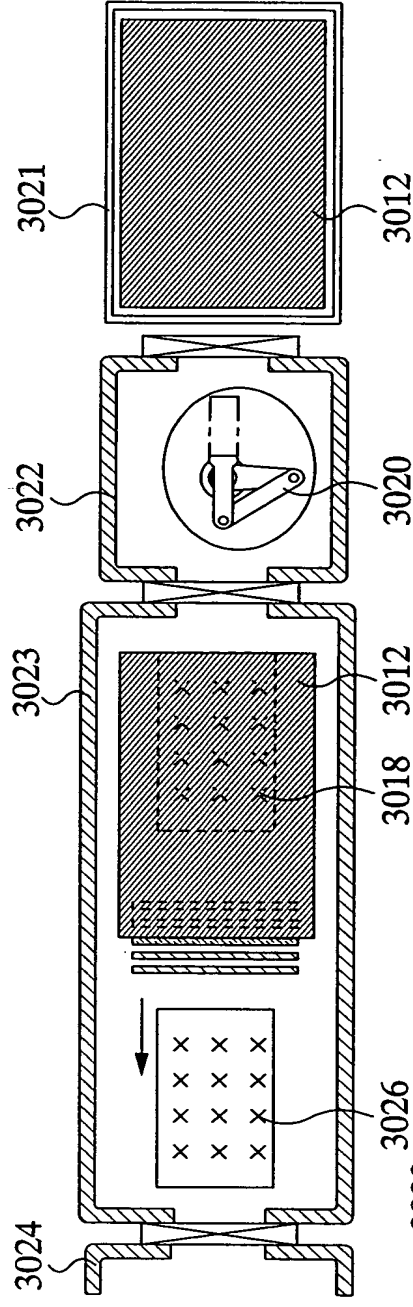


FIG. 8A

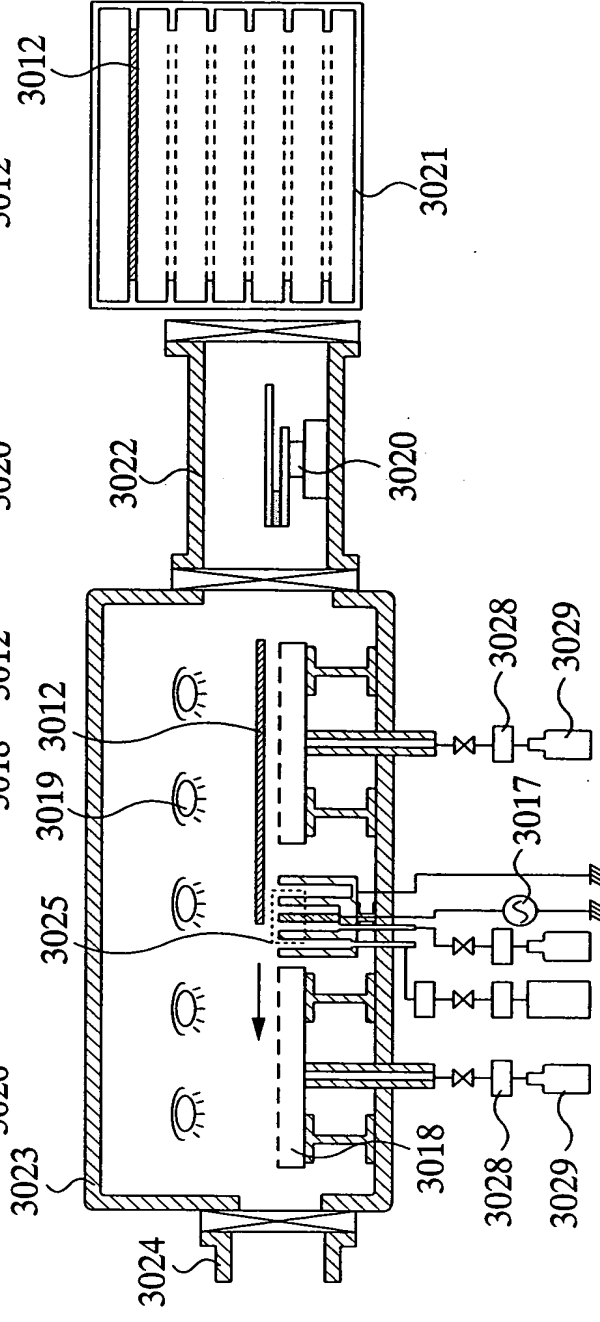


FIG. 8B

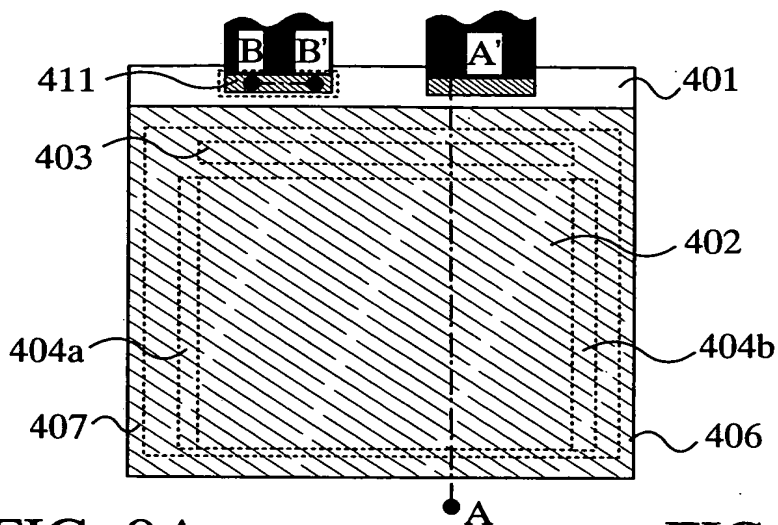


FIG. 9A

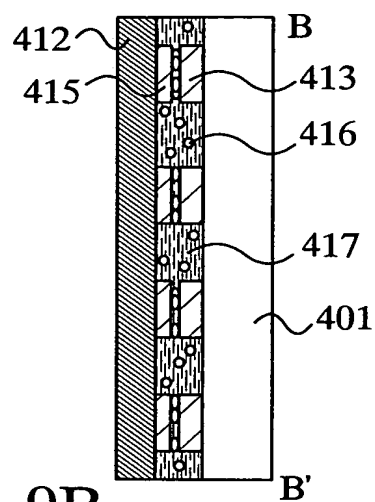


FIG. 9B

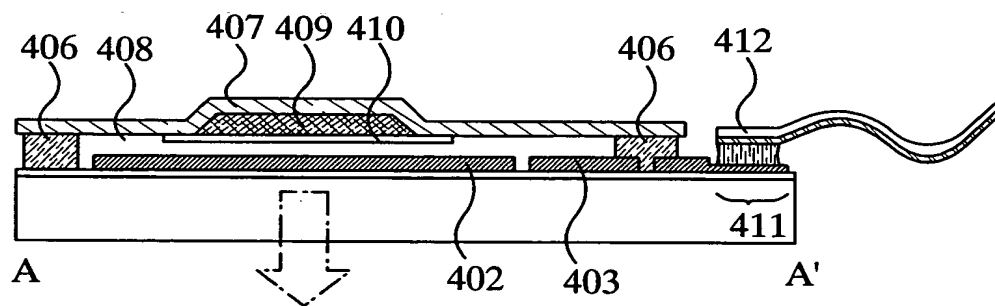


FIG. 9C

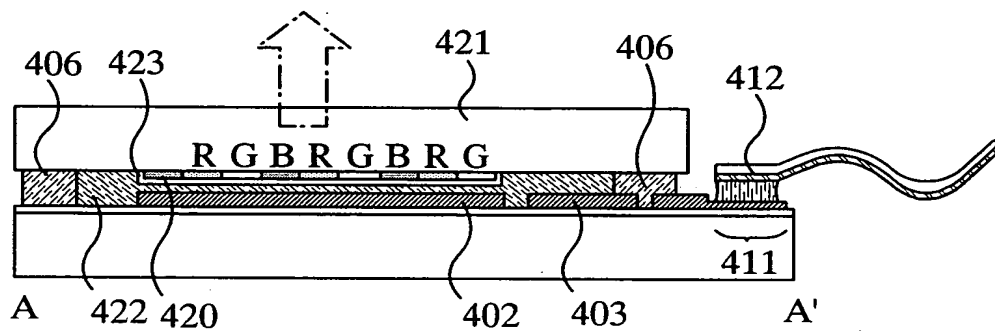
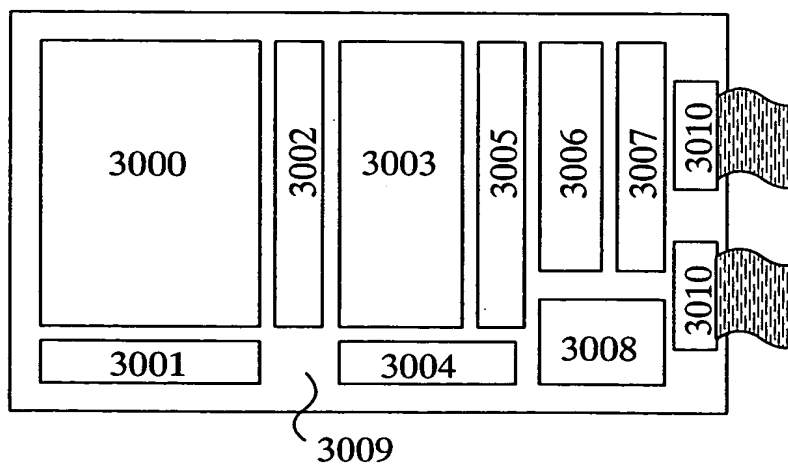


FIG. 9D

FIG. 9E



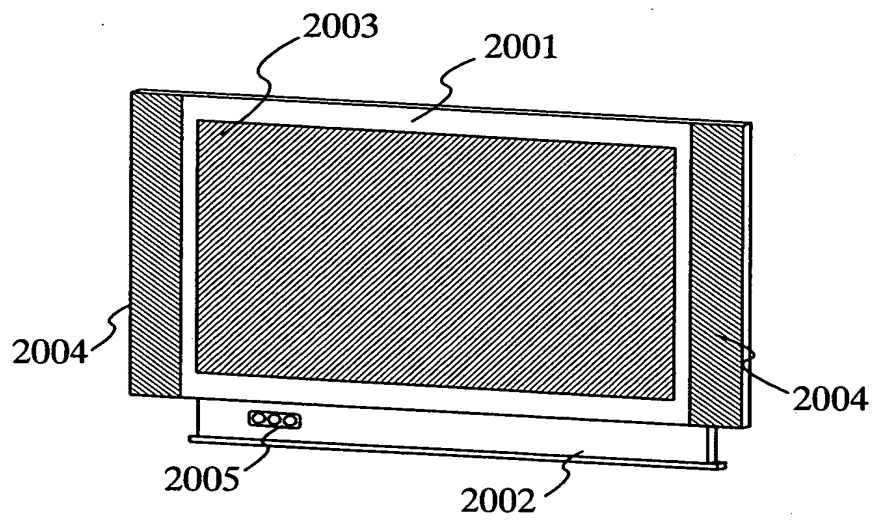


FIG. 10A

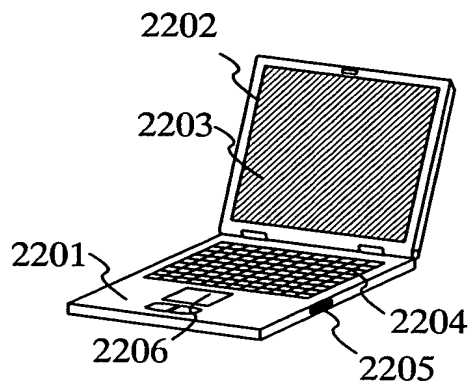


FIG. 10B

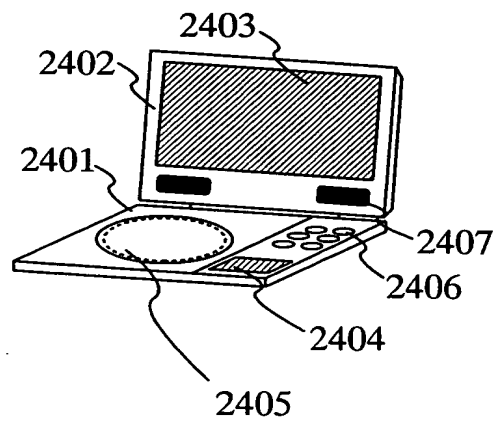


FIG. 10C

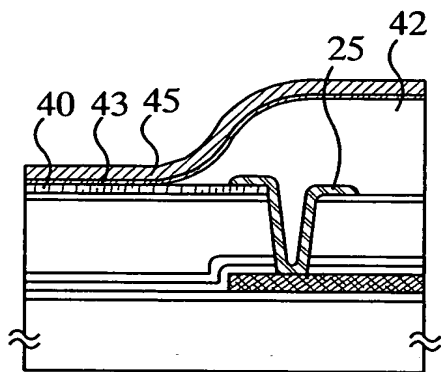


FIG. 11A

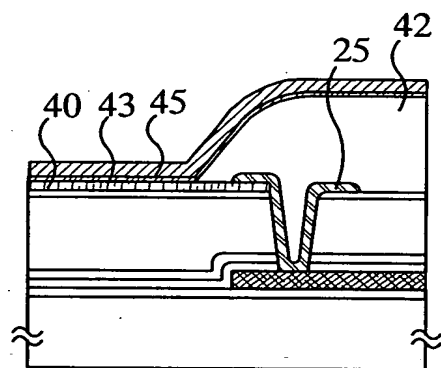


FIG. 11B

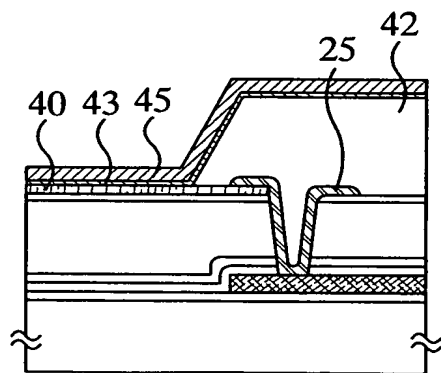


FIG. 11C

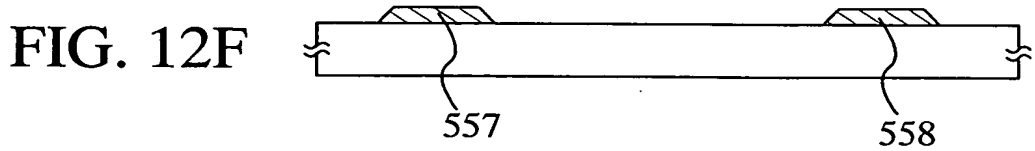
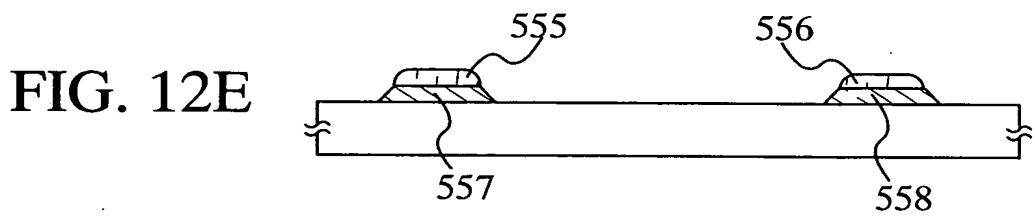
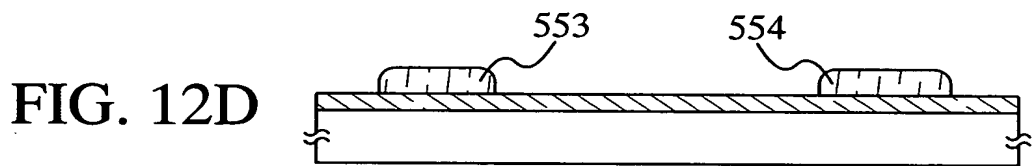
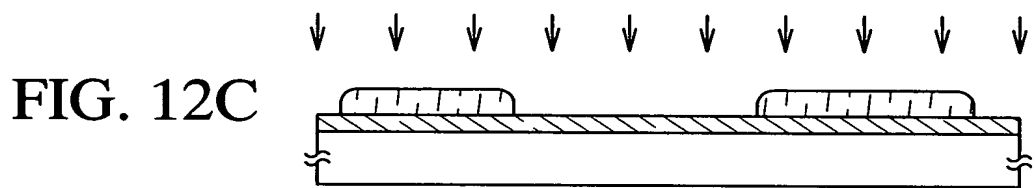
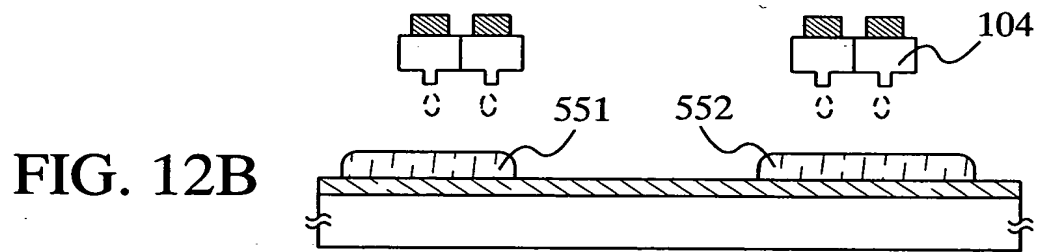
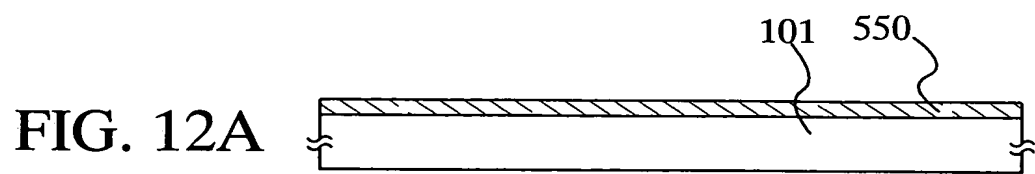


FIG. 13A

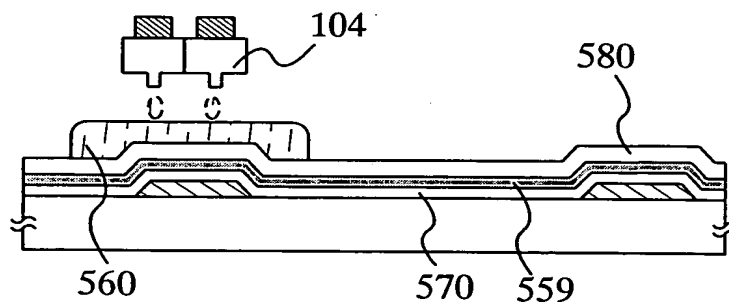


FIG. 13B

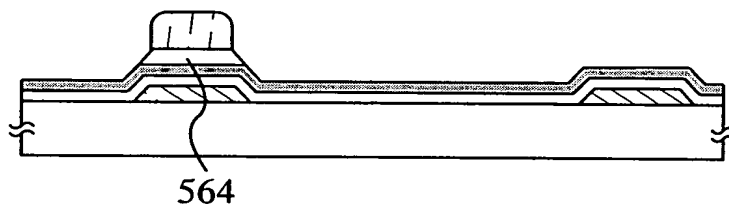


FIG. 13C

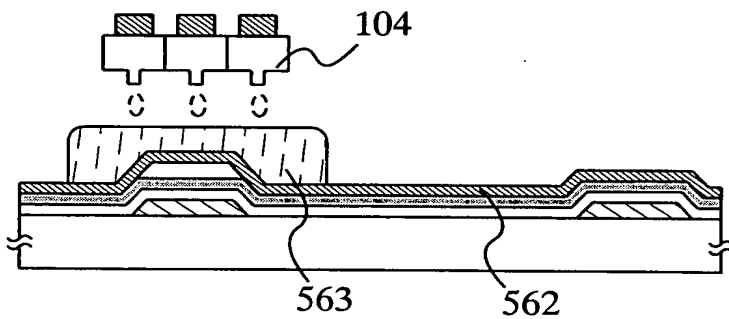
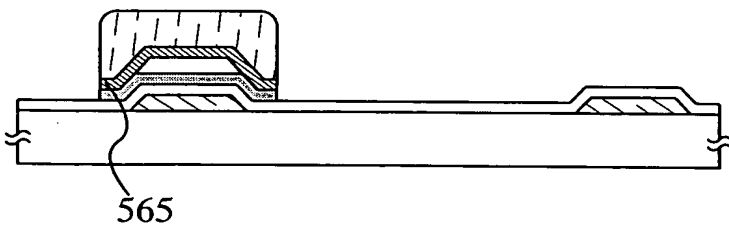
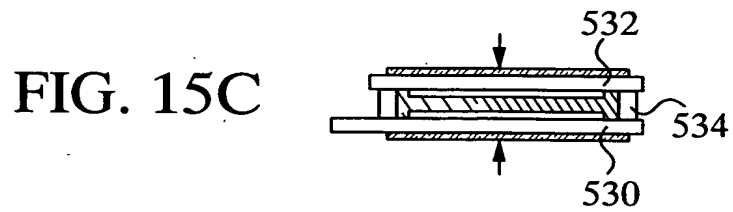
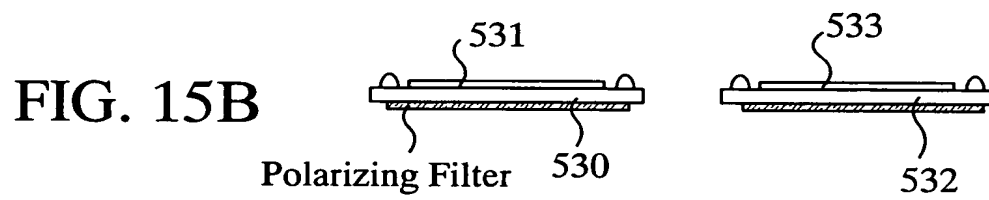
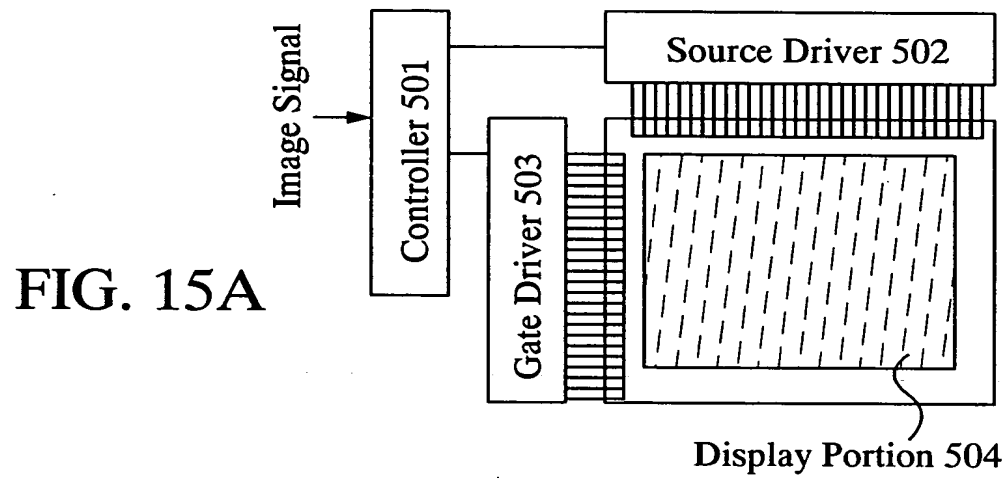


FIG. 13D



A cross-sectional view of a semiconductor device. A substrate is shown with a patterned layer 567 on its top surface. Above the substrate, there is a series of six rectangular contacts 104, each with a central opening. The contacts are arranged in a row, and the patterned layer 567 is visible beneath them.

A cross-sectional view of a semiconductor device. It shows a substrate with a thin layer on top. A patterned layer is formed on the thin layer, with a central rectangular region and two side regions. The side regions are connected to the central region by narrow bridges. The reference numeral 572 points to the right side of the device.



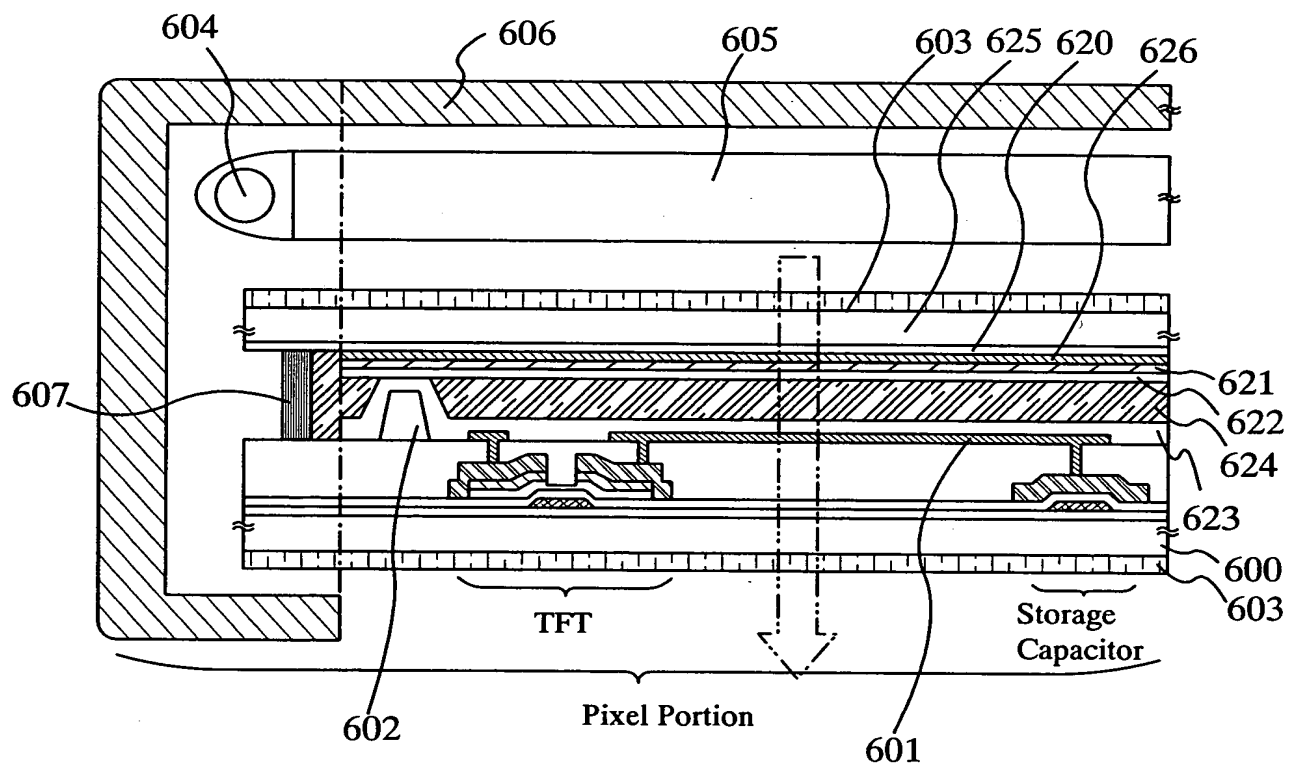


FIG. 16